

# DCR803SG

DS4451-5.0 July 2001

## **Phase Control Thyristor**

Supersedes January 2000 version, DS4451-4.0

#### **FEATURES**

- Double Side Cooling
- High Surge Capability
- High Mean Current
- Fatigue Free

#### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- DC Motor Control

#### **VOLTAGE RATINGS**

Repetitive Peak Voltages V <sub>DRM</sub> V <sub>RRM</sub> V	Conditions
1800	$T_{v_i} = 0^{\circ} \text{ to } 125^{\circ}\text{C},$
1700	$I_{\text{DRM}}^{\text{V}} = I_{\text{RRM}} = 50 \text{mA},$
1600	$V_{\text{DRM}}$ , $V_{\text{RRM}}$ $t_{p}$ = 10ms,
1500	$V_{\text{DSM}} \& V_{\text{RSM}} =$
1400	V <sub>DRM</sub> & V <sub>RRM</sub> + 100V respectively
	Voltages V <sub>DRM</sub> V <sub>RRM</sub> V 1800 1700 1600 1500

Lower voltage grades available.

#### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

#### DCR806SG26

Note: Please use the complete part number when ordering and quote this number in any future correspondance relating to your order. 
 KEY PARAMETERS

 V<sub>DRM</sub>
 1800V

 I<sub>T(AV)</sub>
 1045A

 I<sub>TSM</sub>
 14000A

 dVdt
 1000V/μs

 dI/dt
 1000A/μs

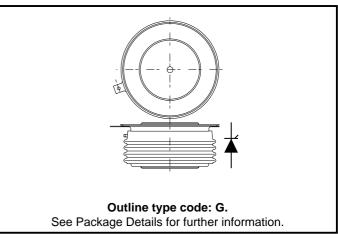


Fig. 1 Package outline



## **CURRENT RATINGS**

T<sub>case</sub> = 60°C unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units			
Double Sid	Double Side Cooled						
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	1045	А			
I <sub>T(RMS)</sub>	RMS value	-	1641	А			
Ι <sub>τ</sub>	Continuous (direct) on-state current	-	1450	А			
Single Side	Single Side Cooled (Anode side)						
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	675	А			
I <sub>T(RMS)</sub>	RMS value	-	1060	Α			
Ι <sub>τ</sub>	Continuous (direct) on-state current	-	862	А			

#### **CURRENT RATINGS**

## T<sub>case</sub> = 80°C unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units			
Double Sid	Double Side Cooled						
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	820	А			
I <sub>T(RMS)</sub>	RMS value	-	1285	А			
I <sub>T</sub>	Continuous (direct) on-state current	-	1085	А			
Single Side Cooled (Anode side)							
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	505	А			
I <sub>T(RMS)</sub>	RMS value	-	793	А			
Ι <sub>τ</sub>	Continuous (direct) on-state current	-	620	А			



#### SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine; T <sub>case</sub> = 125°C	11.2	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_{R} = 50\% V_{RRM} - 1/4 \text{ sine}$	625 x 10 <sup>3</sup>	A²s
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine; T <sub>case</sub> = 125°C	14.0	kA
l²t	I <sup>2</sup> t for fusing	V <sub>R</sub> = 0	975 x 10 <sup>3</sup>	A <sup>2</sup> s

## THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions			Max.	Units
	Thermal resistance - junction to case	Double side cooled	dc	-	0.032	°C/W
$R_{th(j-c)}$		Single side cooled	Anode dc	-	0.064	°C/W
			Cathode dc	-	0.064	°C/W
	Thermal resistance - case to heatsink	Clamping force 12.5kN with mounting compound	Double side	-	0.008	°C/W
R <sub>th(c-h)</sub>			Single side	-	0.016	°C/W
	Virtual junction temperature	On-state (conducting)		-	135	°C
$T_{vj}$		Reverse (blocking)		-	125	°C
T <sub>stg</sub>	Storage temperature range			-55	125	°C
-	Clamping force			11.0	13.0	kN



### **DYNAMIC CHARACTERISTICS**

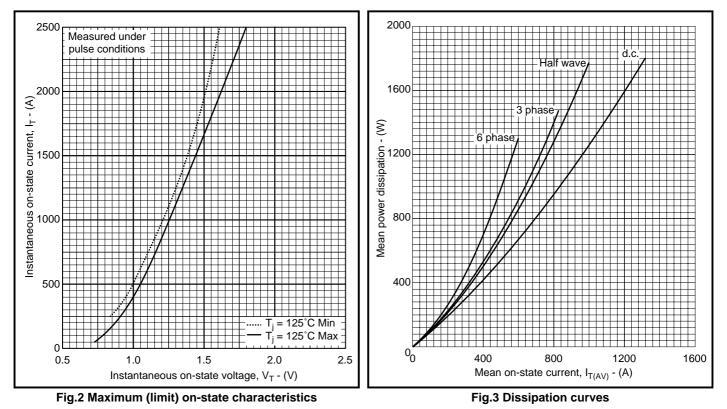
Symbol	Parameter	Conditions		Тур.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At $V_{RRM}/V_{DRM}$ , $T_{case} = 125^{\circ}C$		-	50	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% $V_{DRM} T_j = 125^{\circ}C$ . Gate open circuit.		-	1000	V/µs
		Gate source 1.5A	Repetitive 50Hz	-	500	A/μs
dl/dt	Rate of rise of on-state current		Non-repetitive	-	1000	A/μs
V <sub>T(TO)</sub>	Threshold voltage	At T <sub>vj</sub> = 125°C		-	0.85	V
r <sub>T</sub>	On-state slope resistance	At T <sub>vj</sub> = 125°C		-	0.38	mΩ
t <sub>gd</sub>	Delay time	$V_{D} = 67\% V_{DRM}$ , Gate source 30V, 15 $\Omega$ t <sub>r</sub> = 0.5 $\mu$ s, T <sub>j</sub> = 25°C		-	1.5	μs
t <sub>q</sub>	Turn-off time	$ \begin{split} & I_{_{T}} = 1000\text{A},  t_{_{p}} = 1\text{ms},  T_{_{j}} = 125^{\circ}\text{C}, \\ & V_{_{R}} = 50\text{V},  \text{d}I_{_{RR}}/\text{d}t = 20\text{A}/\mu\text{s}, \\ & V_{_{DR}} = 67\%   \text{V}_{_{DRM}},  \text{d}V_{_{DR}}/\text{d}t = 20\text{V}/\mu\text{s}  \text{linear} \end{split} $		200	300	μs
I <sub>L</sub>	Latching current	$T_{j} = 25^{\circ}C, V_{D} = 5V$		350	1000	mA
I <sub>H</sub>	Holding current	$T_{j} = 25^{\circ}C, V_{D} = 5V$		40	100	mA

#### GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions		Max.	Units
V <sub>GT</sub>	Gate trigger voltage	$V_{\text{DRM}} = 5V, T_{\text{case}} = 25^{\circ}\text{C}$	1.0	3.5	V
I <sub>GT</sub>	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	-	200	mA
V <sub>gd</sub>	Gate non-trigger voltage	At $V_{DRM} T_{case} = 125^{\circ}C$	-	0.25	V
I <sub>GD</sub>	Gate non-trigger current	At V <sub>DRM</sub> T <sub>case</sub> = 125°C	-	-	А
V <sub>FGM</sub>	Peak forward gate voltage	Anode positive with respect to cathode	-	30	V
V <sub>fgn</sub>	Peak forward gate voltage	Anode negative with respect to cathode	-	0.25	V
V <sub>rgm</sub>	Peak reverse gate voltage		-	5	V
I <sub>FGM</sub>	Peak forward gate current	Anode positive with respect to cathode	-	30	А
P <sub>GM</sub>	Peak gate power	See table, gate characteristics curve	-	150	W
P <sub>G(AV)</sub>	Mean gate power		-	10	W



#### **CURVES**

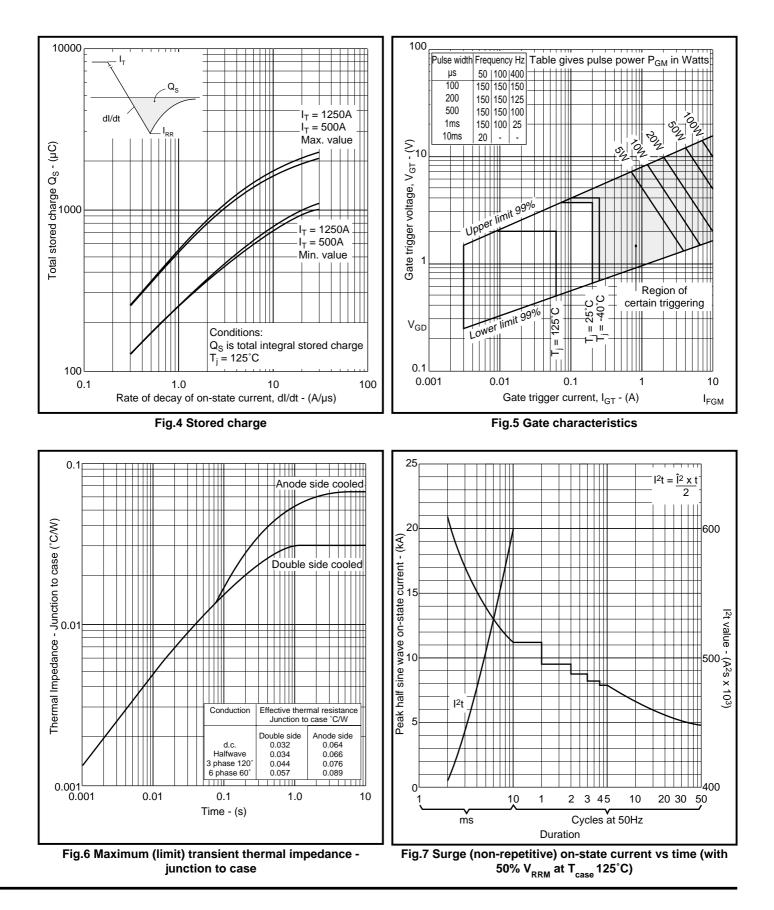


 $V_{TM}$  Equation:-

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = 0.464203 B = 0.51516 C = 0.000249 D = 0.005951 these values are valid for  $T_j = 125$  °C for  $I_T$  500A to 2500A

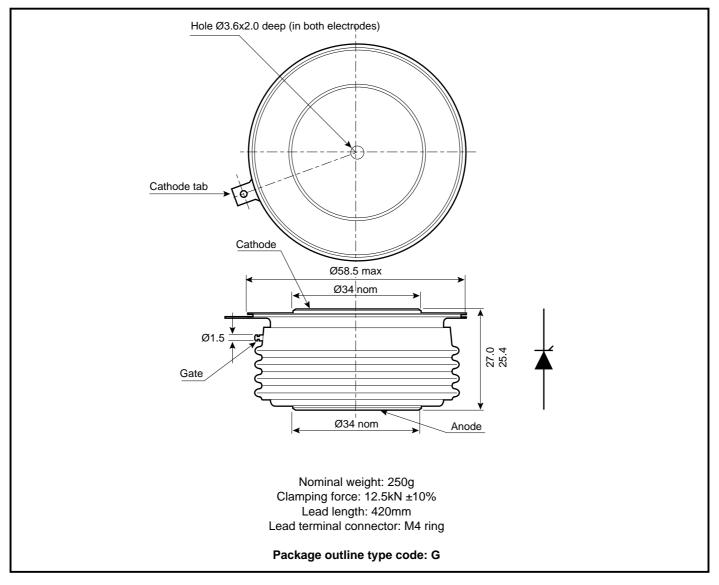






#### **PACKAGE DETAILS**

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





#### POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink / clamping systems in line with advances in device types and the voltage and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the up to date CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete solution (PACs).

#### **DEVICE CLAMPS**

Disc devices require the correct clamping force to ensure their safe operation. The PACs range offers a varied selection of pre-loaded clamps to suit all of our manufactured devices. This include cube clamps for single side cooling of 'T' 22mm

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

#### **HEATSINKS**

Power Assembly has its own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance or our semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest Sales Representative or Customer Services.



#### Datasheet Annotations:

Dynex Semiconductor annotate datasheets in the top right hard corner of the front page, to indicate product status. The annotations are as follows:-

Target Information: This is the most tentative form of information and represents a very preliminary specification. No actual design work on the product has been started.

Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

This publication is issued to provide information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose nor form part of any order or contract nor to be regarded as a representation relating to the products or services concerned. No warranty or guarantee express or implied is made regarding the capability, performance or suitability of any product or service. The Company reserves the right to alter without prior notice the specification, design or price of any product or service. Information concerning possible methods of use is provided as a guide only and does not constitute any guarantee that such methods of use will be satisfactory in a specific piece of equipment. It is the user's responsibility to fully determine the performance and suitability of any equipment using such information and to ensure that any publication or deat used is up to date and has not been superseded. These products are not suitable for use in any medical products whose failure to perform may result in significant injury or death to the user. All products and materials are sold and services provided subject to the Company's conditions of sale, which are available on request.

All brand names and product names used in this publication are trademarks, registered trademarks or trade names of their respective owners.